

### 2SA608 TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$$P_{CM} : 400 \text{ mW (Tamb=25°C)}$$

Collector current

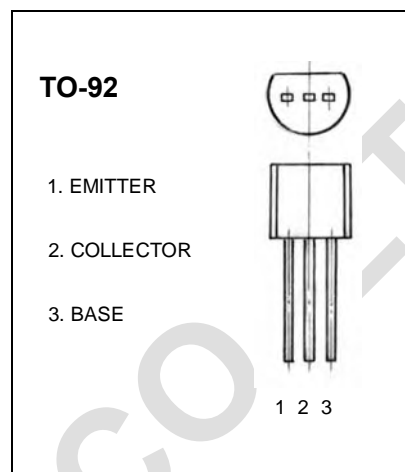
$$I_{CM} : -100 \text{ mA}$$

Collector-base voltage

$$V_{(BR)CBO} : -40 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55°C \text{ to } +150°C$$



#### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-30			V
Emitter-Base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -25V, I_E = 0$			-1	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -4V, I_C = 0$			-1	$\mu A$
DC current gain	$h_{FE}$	$V_{CE} = -6V, I_C = -1mA$	60		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50mA, I_B = -5mA$			-0.5	V
Transition frequency	$f_T$	$V_{CE} = -6V, I_C = -10mA$		180		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -6V, f = 1MHz$		7		pF

#### CLASSIFICATION OF $h_{FE}$

Rank	D	E	F	G
Range	60-120	100-200	160-320	280-560